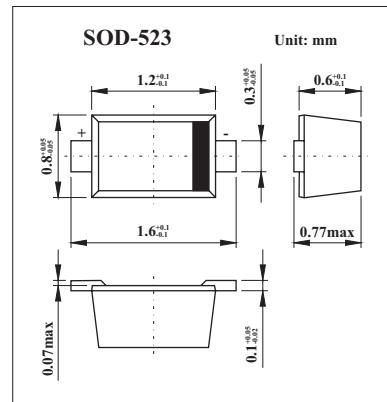


SCHOTTKY BARRIER DIODE

1PS79SB40

■ Features

- Very Low forward voltage
- Guard ring protected
- Ultra small plastic SMD package.
- Low diode capacitance.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
continuous reverse voltage	V _R			40	V
continuous forward current	I _F			120	mA
repetitive peak forward current	I _{FSM}	t _p ≤ 1 s; δ ≤ 0.5		120	mA
non-repetitive peak forward current	I _{FSM}	t _p < 10 ms		200	mA
storage temperature	T _{stg}		-65	+150	°C
junction temperature	T _J			150	°C
operating ambient temperature	T _{amb}		-65	+150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Max	Unit
continuous forward voltage	V _F	I _F = 1 mA	380	mV
		I _F = 10 mA	500	mV
		I _F = 40 mA	1	V
capacitance reverse current	I _R	V _R = 30 V, note 1	1	μ A
		V _R = 40 V, note 1	10	
diodes capacitance	C _d	V _R = 0 V, f = 1 MHz	5	pF

Note

1. Pulse test: t_p = 300 μ s, δ = 0.02.

■ Marking

Marking	T
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